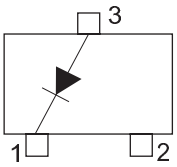
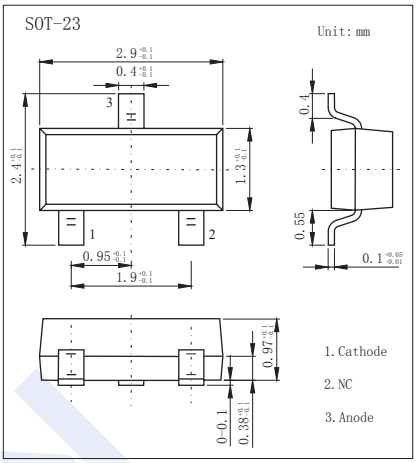
Switching Diodes

HSM223C

■ Features

- Low Capacitance,Proof against High Voltage.
- Fast recovery time.
- MPAK Package is suitable for high density surface mounting and high speed assembly.





■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Reverse voltage	V_R	80	V
Peak voltage	V_{RM}	85	
Average rectified current	Io	100	mA
Peak forward surge current	I_{FM}	300	
Non-repetitive peak forward surge current	I_{FSM}	4	A
Junction Temperature	T_J	125	℃
Storage temperature range	T_{stg}	-55 to 125	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	I_R= 100 uA	80			V
Forward voltage	V_{F1}	I_F= 10 mA		0.76	1.0	
	V_{F2}	I_F= 50 mA		0.88	1.0	
	V_{F3}	I_F= 100 mA		0.97	1.2	
Reverse voltage leakage current	I_R	V_R= 80V			0.1	uA
Junction capacitance	C_j	V_R= 0 V, f= 1 MHz		0.5	2.0	pF
Reverse recovery time	t_{rr}	I_F=10mA,V_R =6V, R_L=50Ω			3.0	ns

■ Marking

NO.	HSM223C
Marking	A8

Switching Diodes

HSM223C

■ Typical Characterisitics

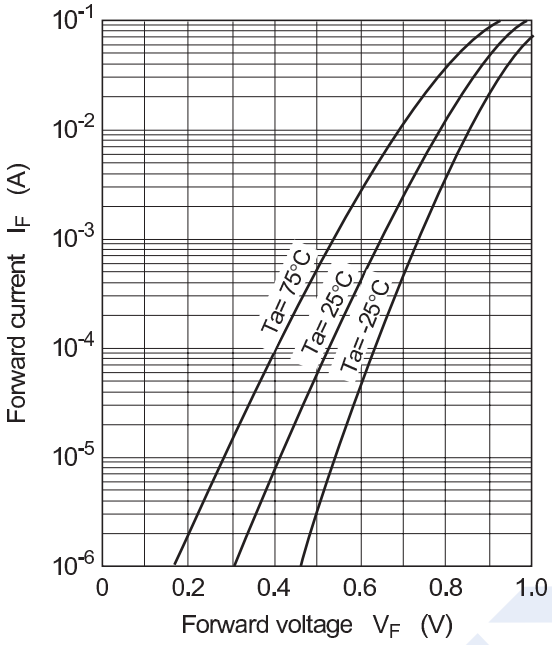


Fig.1 Forward current vs. Forward voltage

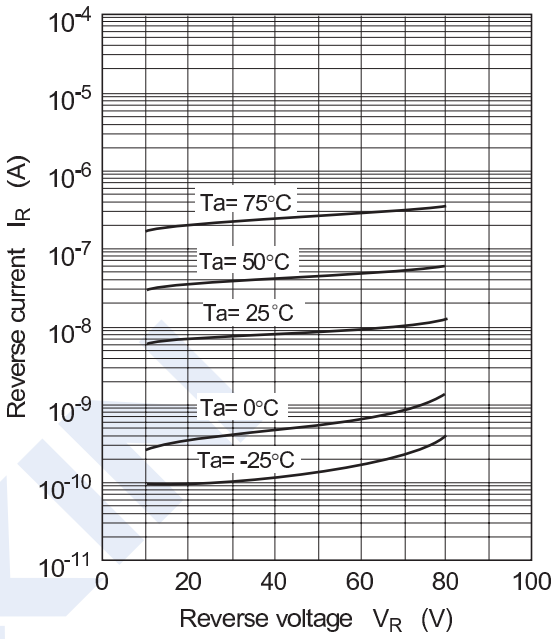


Fig.2 Reverse current vs. Reverse voltage

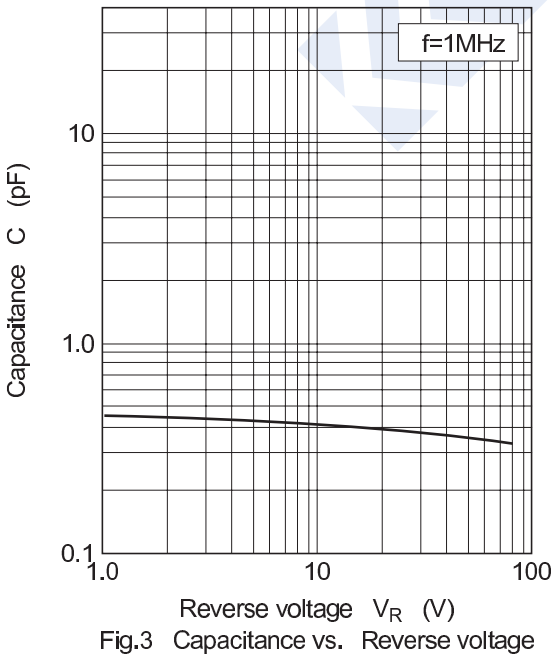


Fig.3 Capacitance vs. Reverse voltage